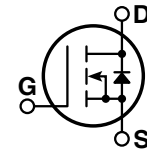


POWER MOS V®

FREDFET


Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.

- Fast Recovery Body Diode
- Lower Leakage
- Faster Switching
- 100% Avalanche Tested
- Popular SOT-227 Package



MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT10M07JVFR	UNIT
V_{DSS}	Drain-Source Voltage	100	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	225	Amps
I_{DM}	Pulsed Drain Current ^①	900	
V_{GS}	Gate-Source Voltage Continuous	± 30	Volts
V_{GSM}	Gate-Source Voltage Transient	± 40	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	700	Watts
	Linear Derating Factor	5.6	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ^① (Repetitive and Non-Repetitive)	225	Amps
E_{AR}	Repetitive Avalanche Energy ^①	50	mJ
E_{AS}	Single Pulse Avalanche Energy ^④	3600	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$)	100			Volts
$I_{D(on)}$	On State Drain Current ^② ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10\text{V}$)	225			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance ^② ($V_{GS} = 10\text{V}, 0.5 I_{D[Cont.]}$)			0.007	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0\text{V}$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0\text{V}, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$)			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 5.0\text{mA}$)	2		4	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

APT10M07JVFR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C _{iss}	Input Capacitance	V _{GS} = 0V		18000	21600	pF
C _{oss}	Output Capacitance	V _{DS} = 25V		6800	9500	
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz		2800	4200	
Q _g	Total Gate Charge ③	V _{GS} = 10V		700	1050	nC
Q _{gs}	Gate-Source Charge	V _{DD} = 0.5 V _{DSS}		130	195	
Q _{gd}	Gate-Drain ("Miller") Charge	I _D = I _D [Cont.] @ 25°C		300	435	
t _{d(on)}	Turn-on Delay Time	V _{GS} = 15V		25	50	ns
t _r	Rise Time	V _{DD} = 0.5 V _{DSS}		60	120	
t _{d(off)}	Turn-off Delay Time	I _D = I _D [Cont.] @ 25°C		80	120	
t _f	Fall Time	R _G = 0.6Ω		20	40	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT	
I _S	Continuous Source Current (Body Diode)			225	Amps	
I _{SM}	Pulsed Source Current ① (Body Diode)			900		
V _{SD}	Diode Forward Voltage ② (V _{GS} = 0V, I _S = -I _D [Cont.])			1.3	Volts	
dv/dt	Peak Diode Recovery dv/dt ⑤			8	V/ns	
t _{rr}	Reverse Recovery Time (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _J = 25°C		150	250	ns
		T _J = 125°C		250	500	
Q _{rr}	Reverse Recovery Charge (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _J = 25°C		0.9		μC
		T _J = 125°C		2.5		
I _{RRM}	Peak Recovery Current (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _J = 25°C		12		Amps
		T _J = 125°C		20		

THERMAL/PACKAGE CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R _{θJC}	Junction to Case			0.18	°C/W
R _{θJA}	Junction to Ambient			40	
V _{isolation}	RMS Voltage (50-60 Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts
Torque	Maximum Torque for Device Mounting Screws and Electrical Terminations.			13	lb•in

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%
- ③ See MIL-STD-750 Method 3471
- ④ Starting T_J = +25°C, L = 142μH, R_G = 25Ω, Peak I_L = 225A

APT Reserves the right to change, without notice, the specifications and information contained herein.

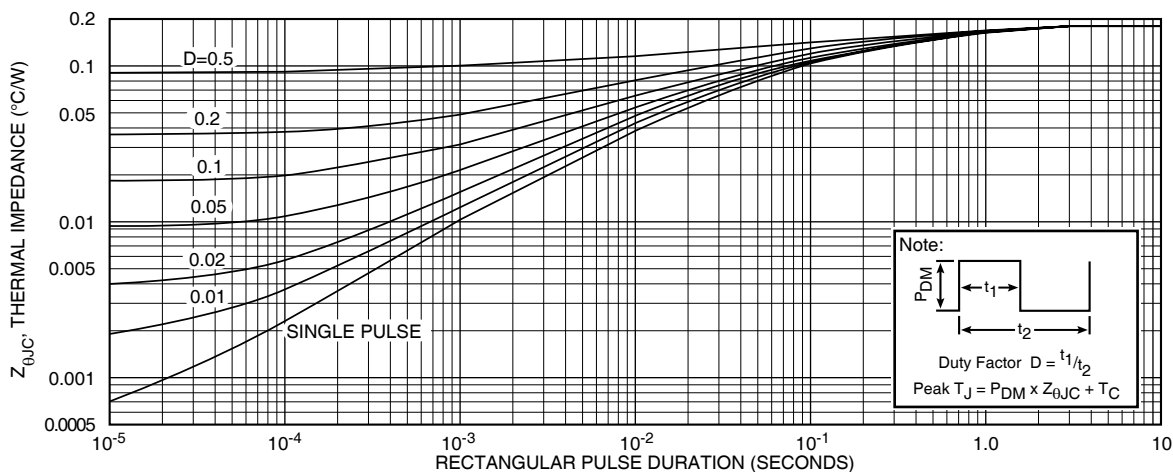


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

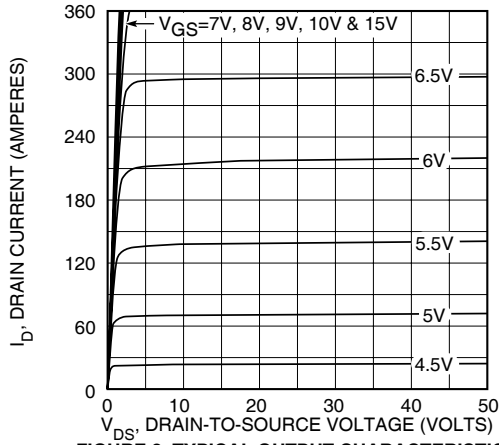


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

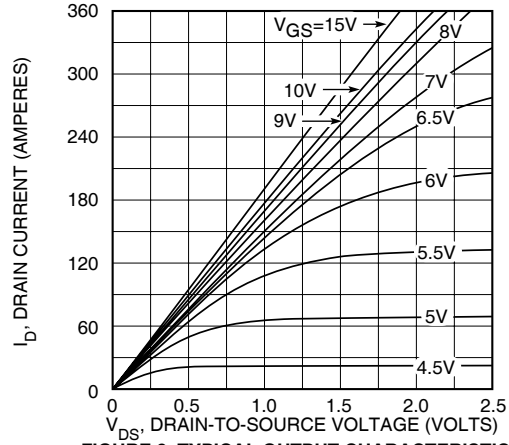


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

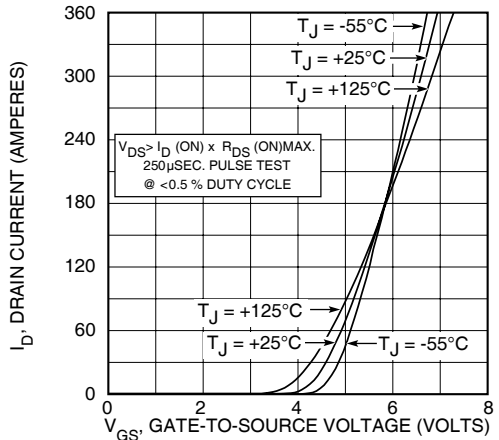


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

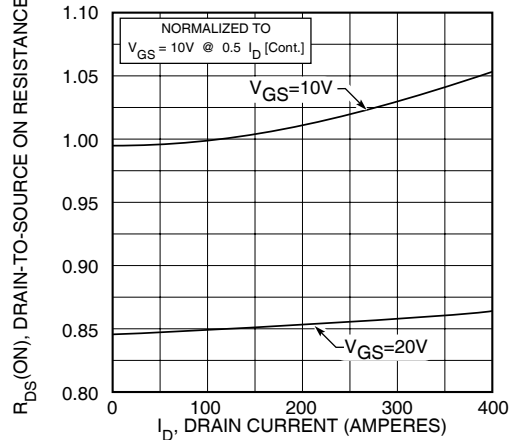


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

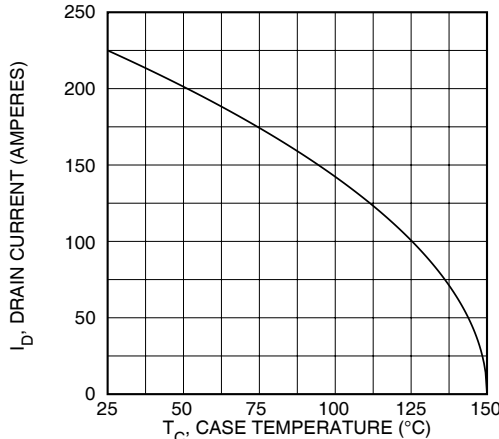


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

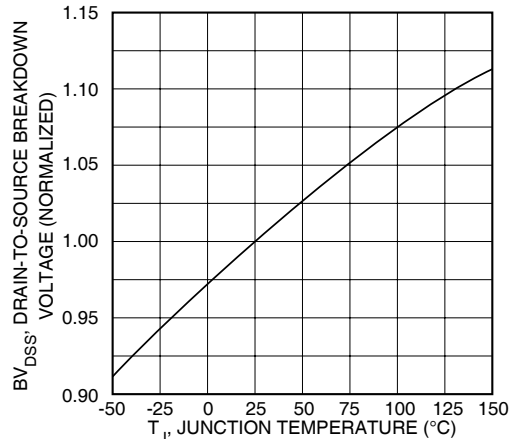


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

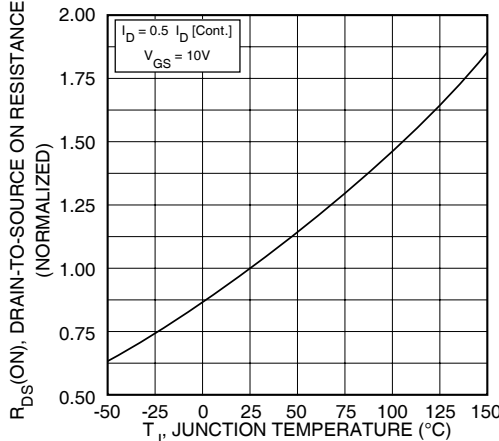


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

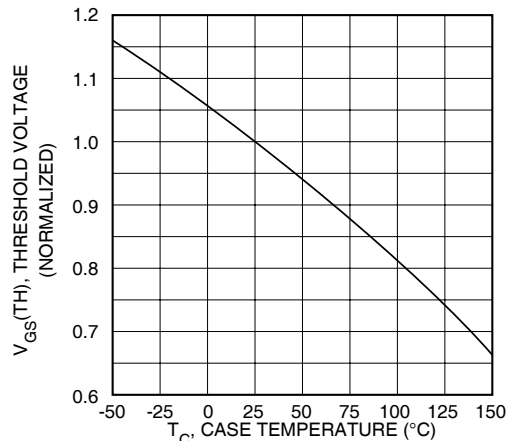


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

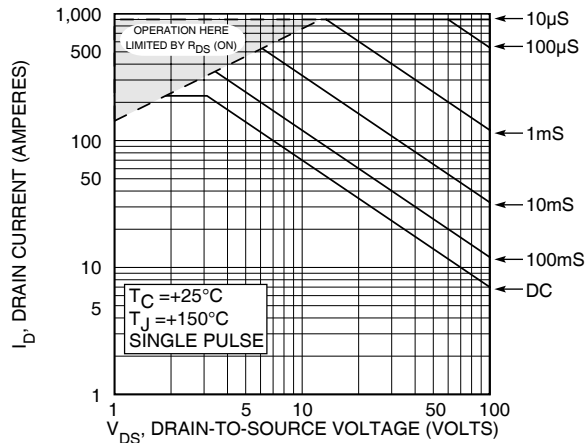


FIGURE 10, MAXIMUM SAFE OPERATING AREA

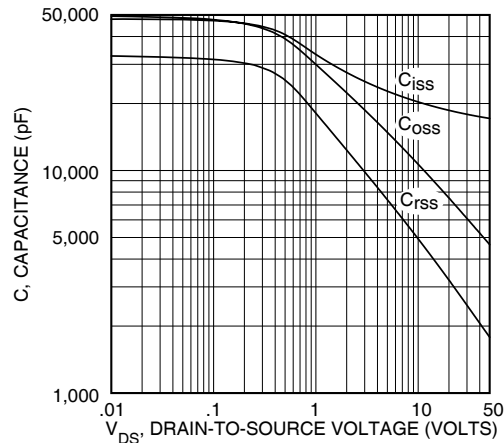


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

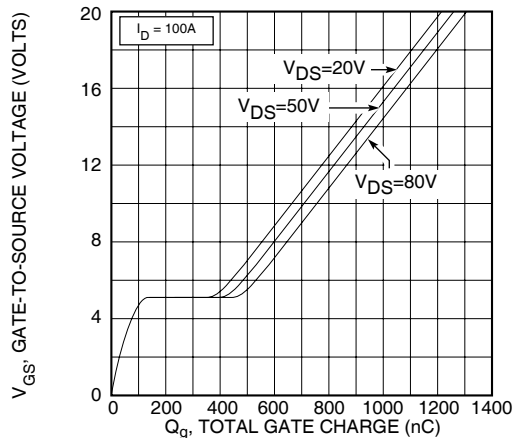


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

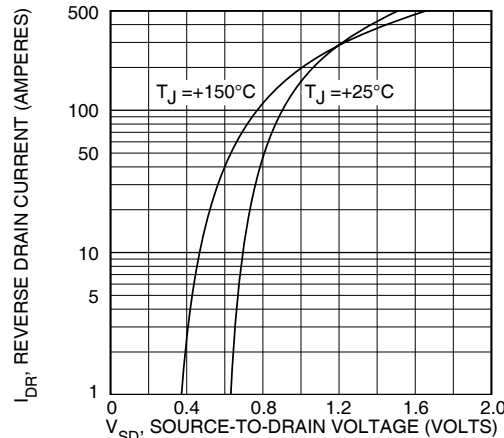
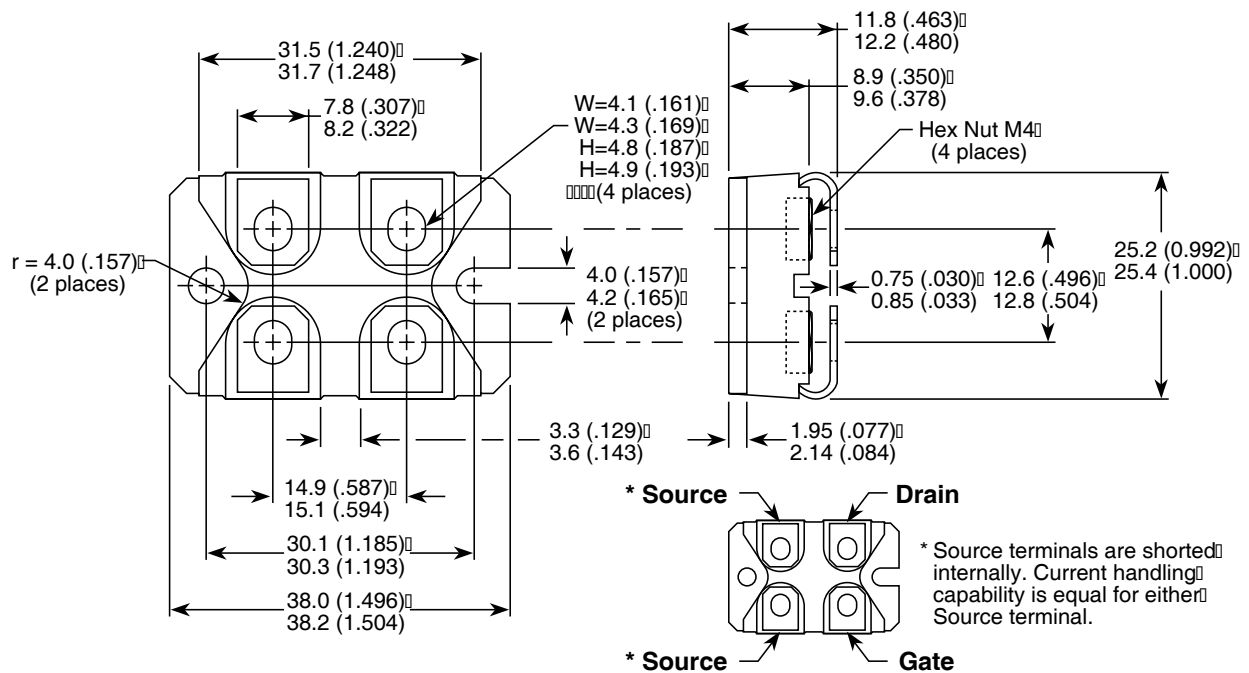


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)